



### Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- External Creepage  $\geq 7.5\text{mm}$  (S/SL Type)
- External Creepage  $\geq 8.0\text{mm}$  (SLM Type)
- Operating temperature range - 55 °C to 110 °C
- Regulatory Approvals
  - UL - UL1577 (E364000)
  - VDE - EN60747-5-5(VDE0884-5)
  - CQC – GB4943.1, GB8898
  - IEC60065, IEC60950

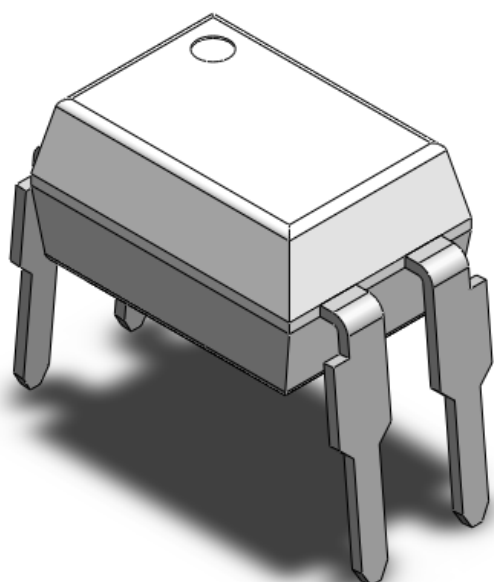
### Description

The CT817 series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 4-lead DIP package different lead forming options.

### Applications

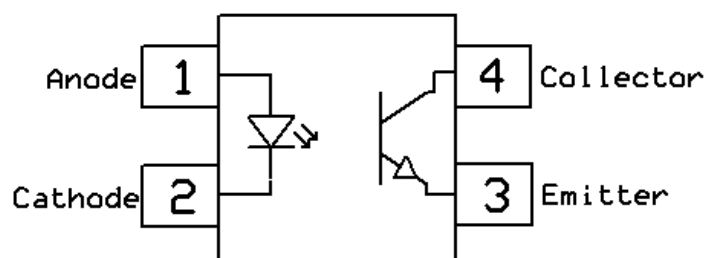
- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

### Package Outline



*Note: Different lead forming options available. See package dimension.*

### Schematic



**Absolute Maximum Rating at 25°C**

<b>Symbol</b>	<b>Parameters</b>	<b>Ratings</b>	<b>Units</b>	<b>Notes</b>
V <sub>ISO</sub>	Isolation voltage	5000	V <sub>RMS</sub>	
P <sub>TOT</sub>	Total power dissipation	200	mW	
T <sub>OPR</sub>	Operating temperature	-55 ~ +110	°C	
T <sub>STG</sub>	Storage temperature	-55 ~ +150	°C	
T <sub>SOL</sub>	Soldering temperature	260	°C	
<b>Emitter</b>				
I <sub>F</sub>	Forward current	60	mA	
I <sub>F(TRANS)</sub>	Peak transient current (≤1μs P.W,300pps)	1	A	
V <sub>R</sub>	Reverse voltage	6	V	
P <sub>D</sub>	Emitter power dissipation	100	mW	
<b>Detector</b>				
P <sub>D</sub>	Detector power dissipation	150	mW	
B <sub>VCEO</sub>	Collector-Emitter Breakdown Voltage	35	V	
B <sub>VECO</sub>	Emitter-Collector Breakdown Voltage	6	V	
I <sub>C</sub>	Collector Current	50	mA	

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  (unless otherwise specified)**Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_F$	Forward voltage	$I_F = 10\text{mA}$	-	1.24	1.4	V	
$I_R$	Reverse Current	$V_R = 6\text{V}$	-	-	5	$\mu\text{A}$	
$C_{IN}$	Input Capacitance	$f = 1\text{MHz}$	-	10	30	pF	

**Detector Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{CEO}}$	Collector-Emitter Breakdown	$I_C = 100\mu\text{A}$	35	-	-	V	
$B_{V_{ECO}}$	Emitter-Collector Breakdown	$I_E = 100\mu\text{A}$	6	-	-	V	
$I_{CEO}$	Collector-Emitter Dark Current	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$	-	-	100	nA	

**Transfer Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes	
CTR	Current Transfer Ratio	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$	CT817	50	-	600	%	
			CT817A	80	-	160		
			CT817B	130	-	260		
			CT817C	200	-	400		
			CT817D	300	-	600		
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_F = 20\text{mA}, I_C = 1\text{mA}$	-	0.1	0.2	V		
$R_{IO}$	Isolation Resistance	$V_{IO} = 500\text{V}_{DC}$	$5 \times 10^{10}$	-	-			
$C_{IO}$	Isolation Capacitance	$f = 1\text{MHz}$	-	0.25	1	pF		

**Switching Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$t_r$	Rise Time	$I_C = 2\text{mA}, V_{CE} = 2\text{V}$	-	6	18	$\mu\text{s}$	
$t_f$	Fall Time	$R_L = 100$	-	8	18		



Typical Characteristic Curves

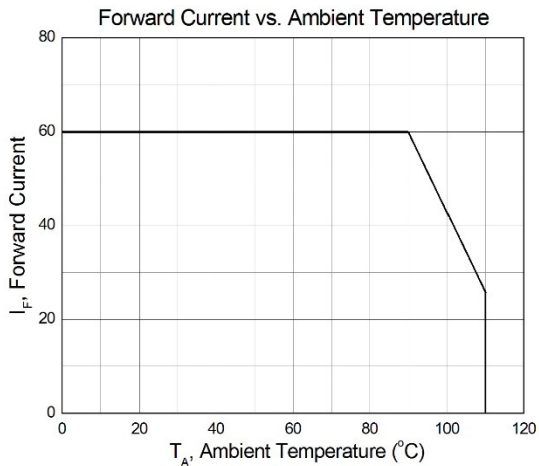


Figure 1

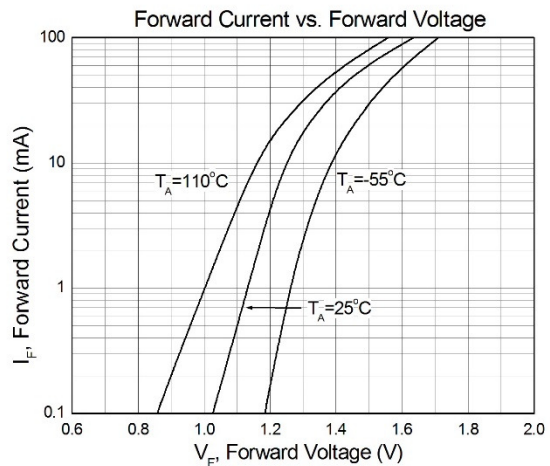


Figure 2

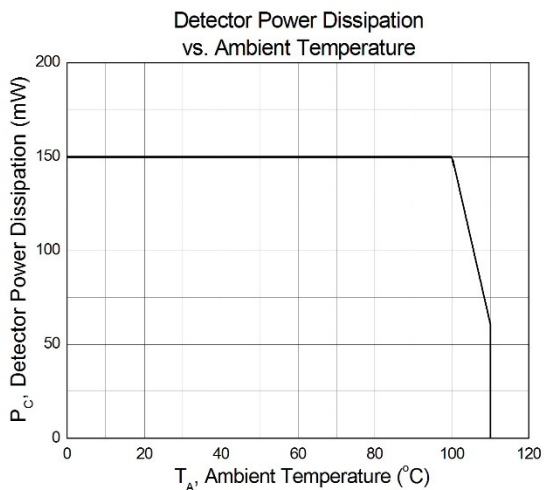


Figure 3

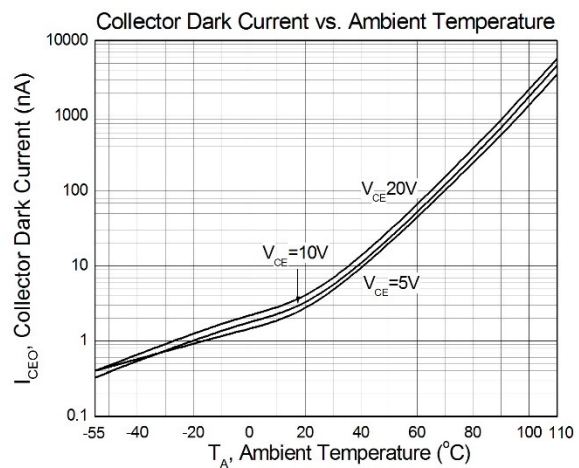


Figure 4

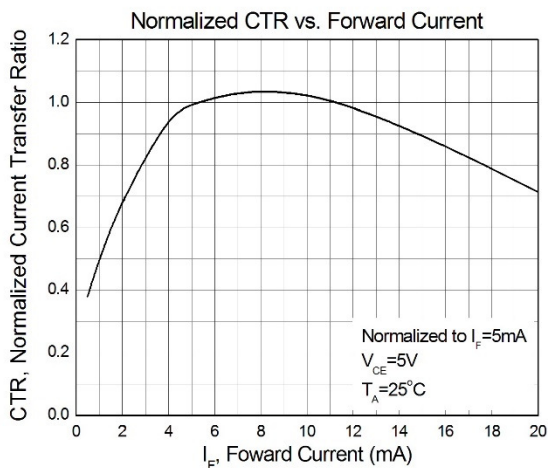


Figure 5

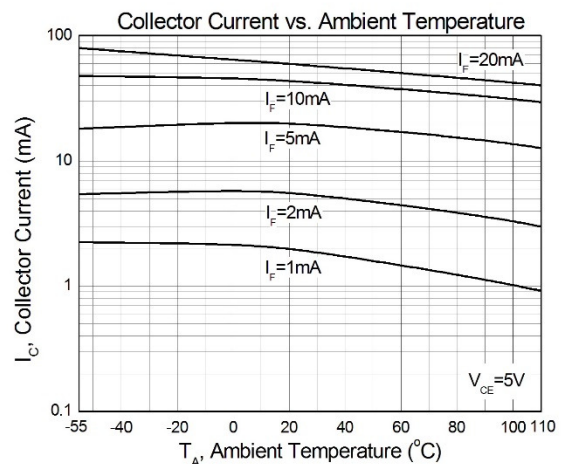


Figure 6

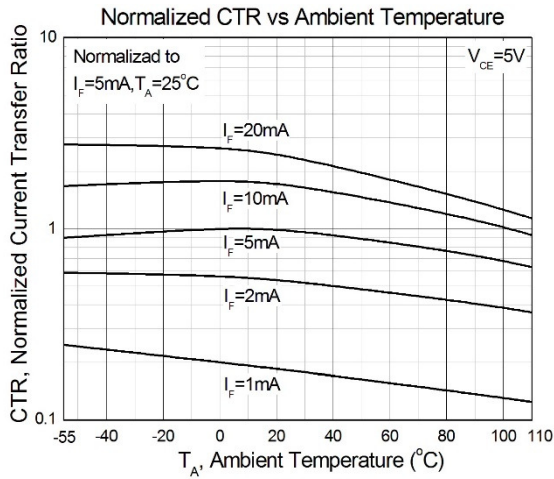


Figure 7

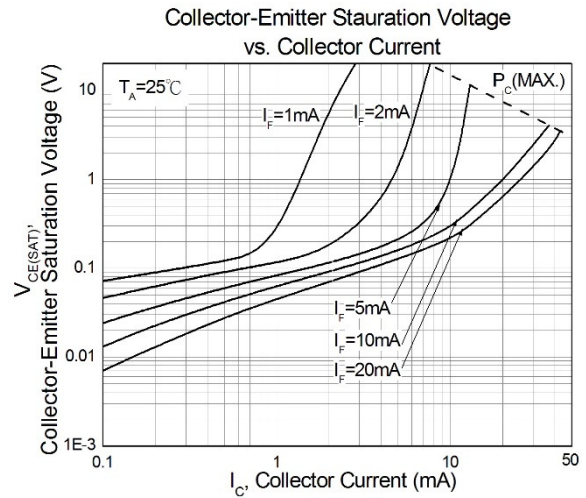


Figure 8

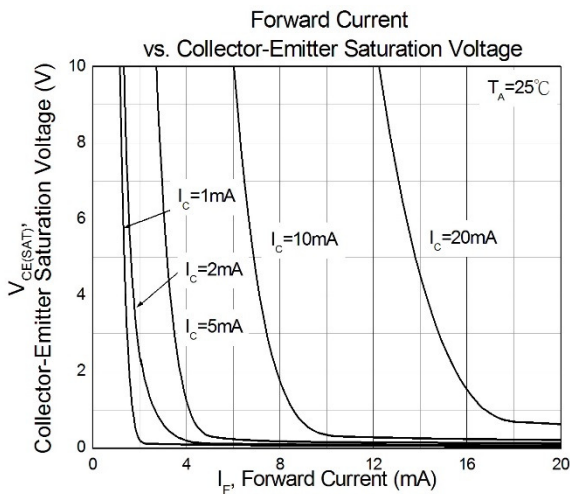


Figure 9

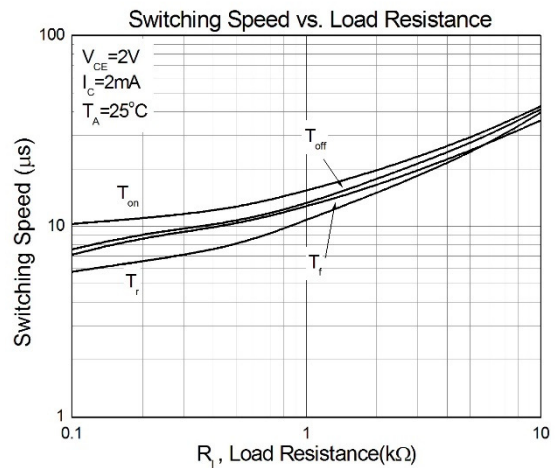


Figure 10

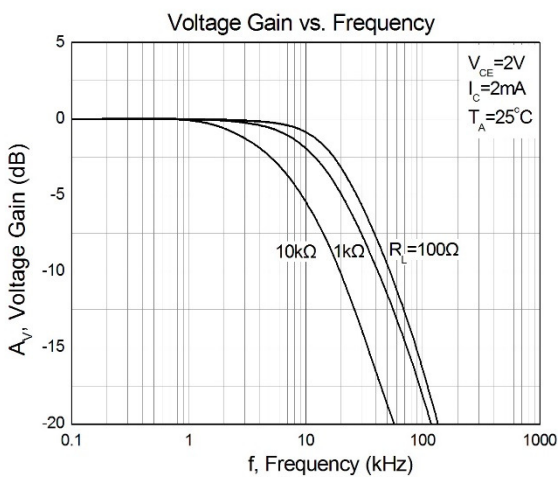


Figure 11



Test Circuit

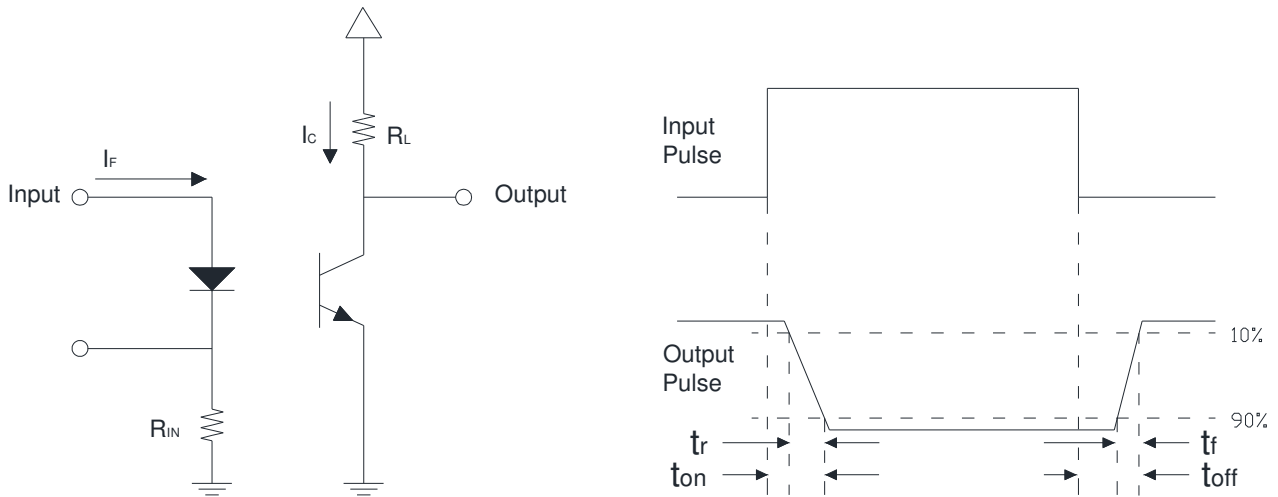
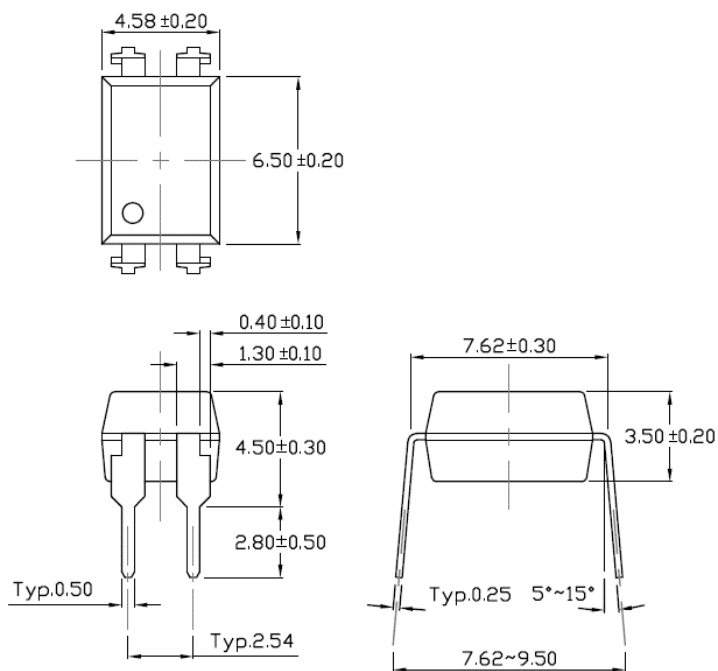


Figure 12: Switching Time Test Circuits

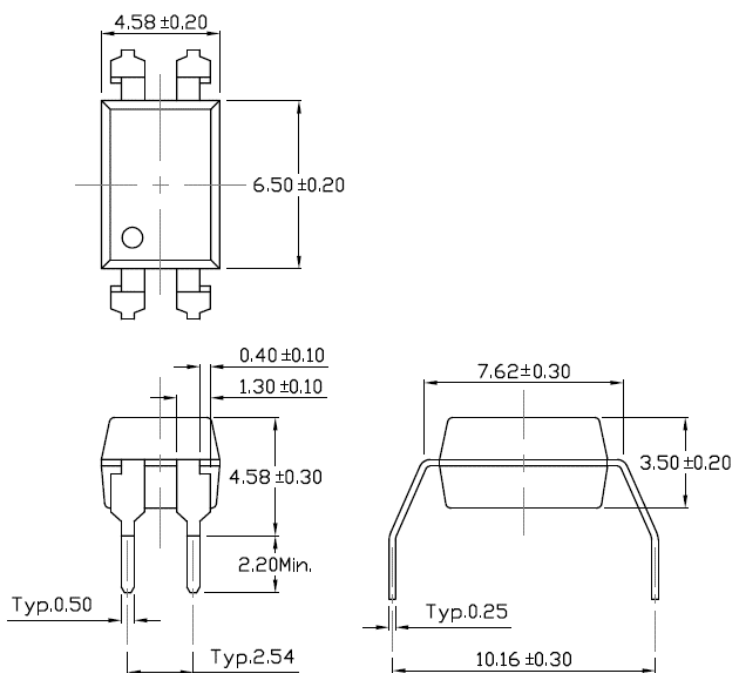


**Package Dimension** *Dimensions in mm unless otherwise stated*

**Standard DIP – Through Hole**

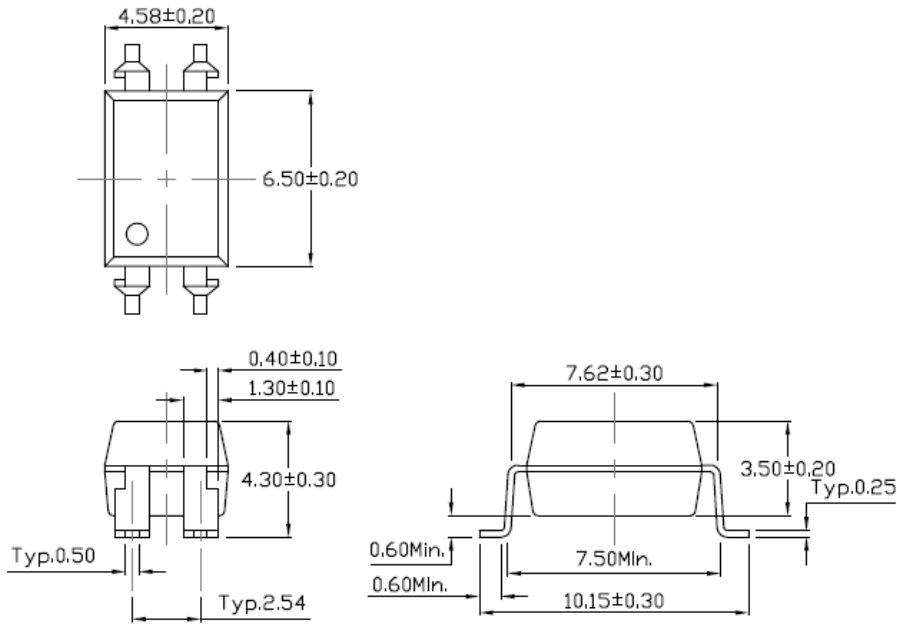


**Gullwing (400mil) Lead Forming – Through Hole (M Type)**

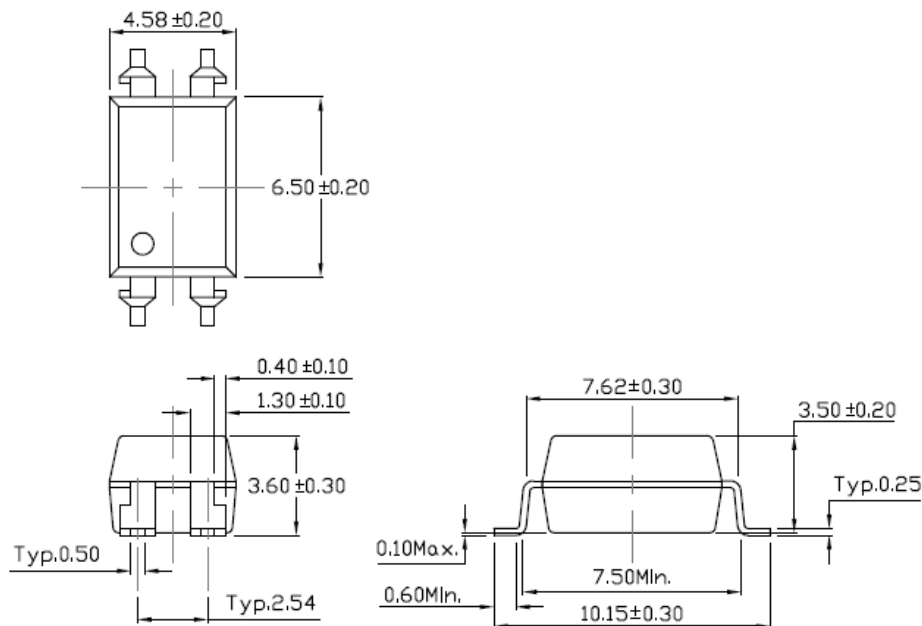




Surface Mount Lead Forming (S Type)



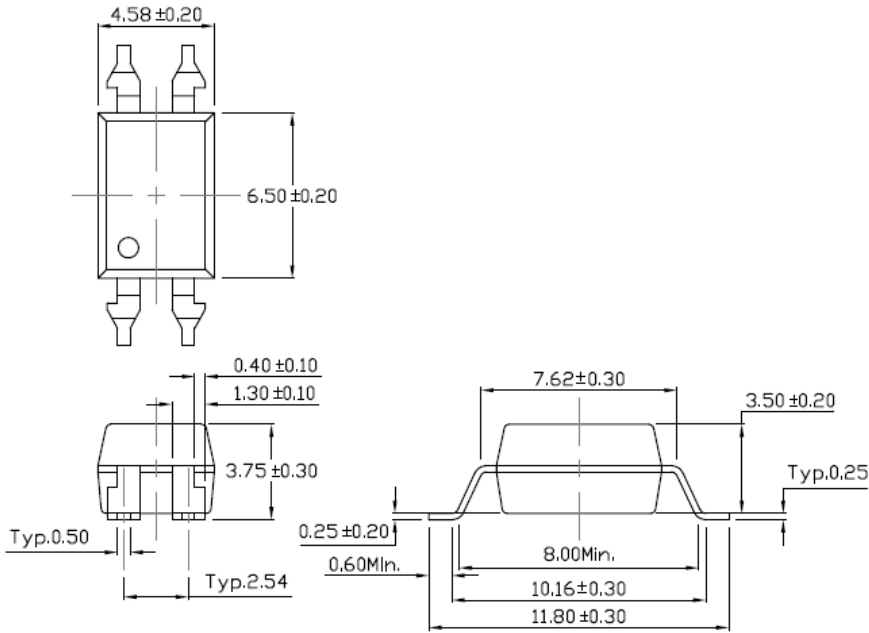
Surface Mount (Low Profile) Lead Forming (SL Type)







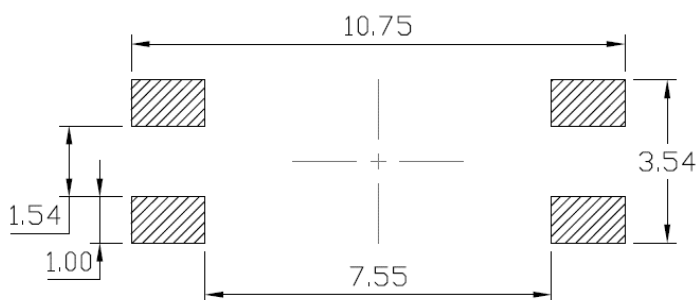
Surface Mount (Gullwing) Lead Forming (SLM Type)



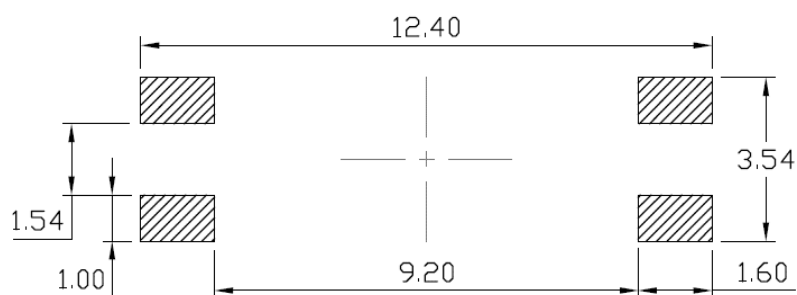


**Recommended Solder Mask** *Dimensions in mm unless otherwise stated*

**Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming**



**Surface Mount (Gullwing) Lead Forming**



**Marking Information**



**Note:**

- CT : Denotes "CT Micro"
- 817 : Part Number
- V : VDE Option
- R : CTR Rank
- Y : Fiscal Year
- WW : Work Week
- K : Manufacturing Code

**Ordering Information****CT817X(V)(Y)(Z)-HG**

X = Part No. (X=A, B, C, D or None)

V = VDE Option ( V or None)

Y = Lead form option (S, SL, M, SLM or none)

Z = Tape and reel option (T1, T2, T3, T4 or none)

H = Lead frame option (H: Iron, None: Copper)

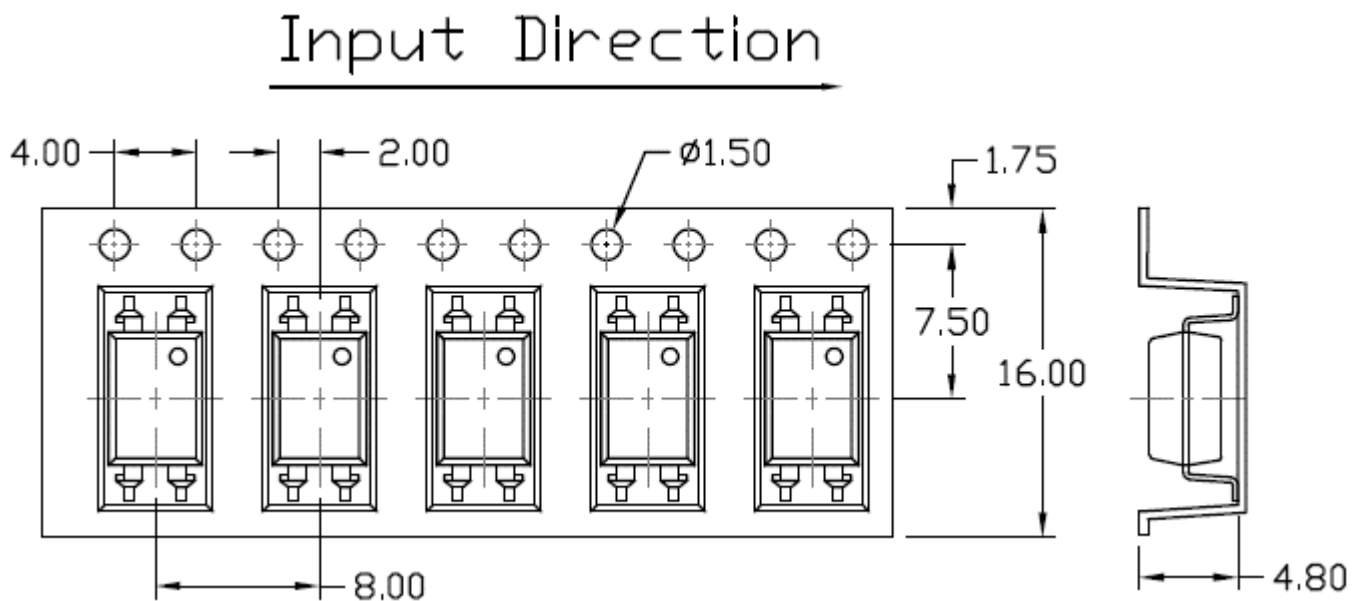
G= Material option (G: Green, None: Non-green)

<b>Option</b>	<b>Description</b>	<b>Quantity</b>
None	Standard 4 Pin Dip	100 Units/Tube
M	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1500 Units/Reel
S(T3)	Surface Mount Lead Forming – With Option 3 Taping	1000 Units/Reel
S(T4)	Surface Mount Lead Forming – With Option 4 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1500 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1500 Units/Reel
SL(T3)	Surface Mount (Low Profile) Lead Forming– With Option 3 Taping	1000 Units/Reel
SL(T4)	Surface Mount (Low Profile) Lead Forming – With Option 4 Taping	1000 Units/Reel
SLM(T1)	Surface Mount (Gullwing) Lead Forming– With Option 1 Taping	1500 Units/Reel
SLM(T2)	Surface Mount (Gullwing) Lead Forming – With Option 2 Taping	1500 Units/Reel

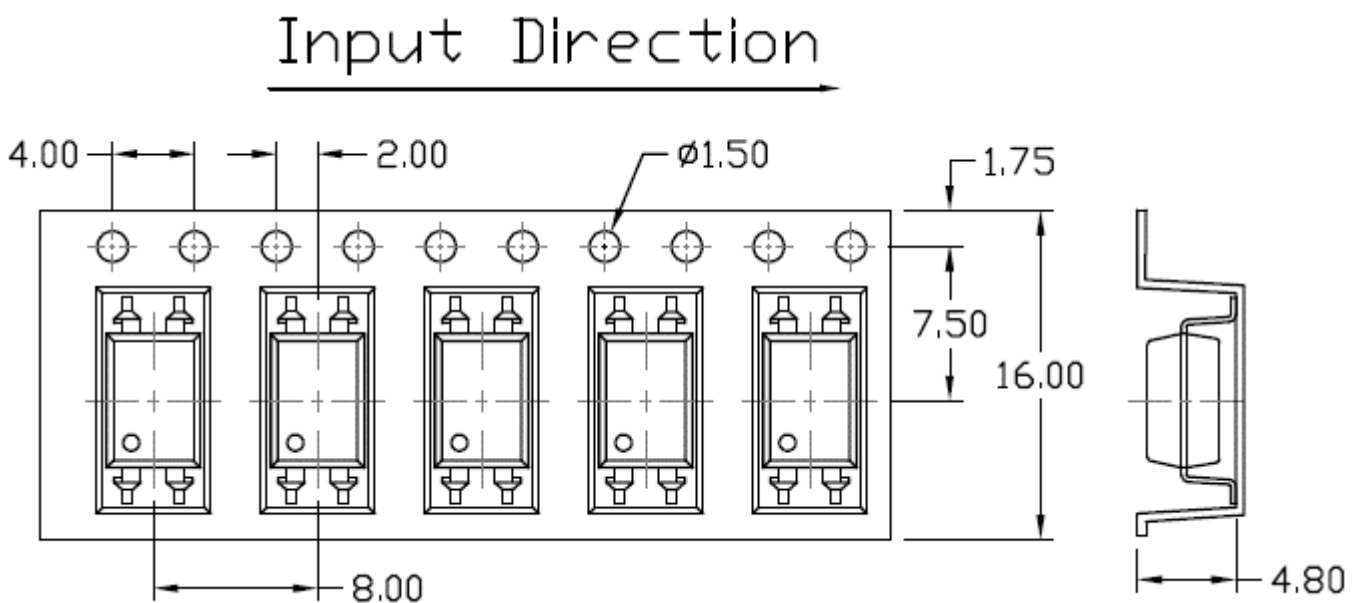


**Carrier Tape Specifications** *Dimensions in mm unless otherwise stated*

**Option S(T1) & SL(T1)**



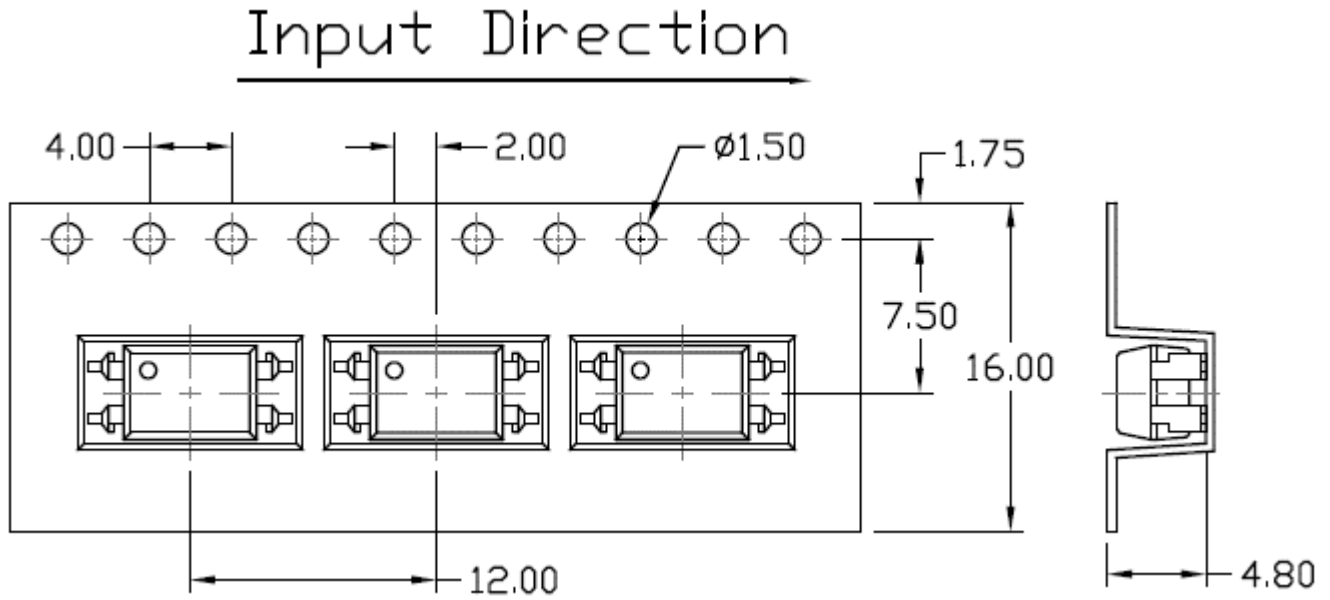
**Option S(T2) & SL(T2)**



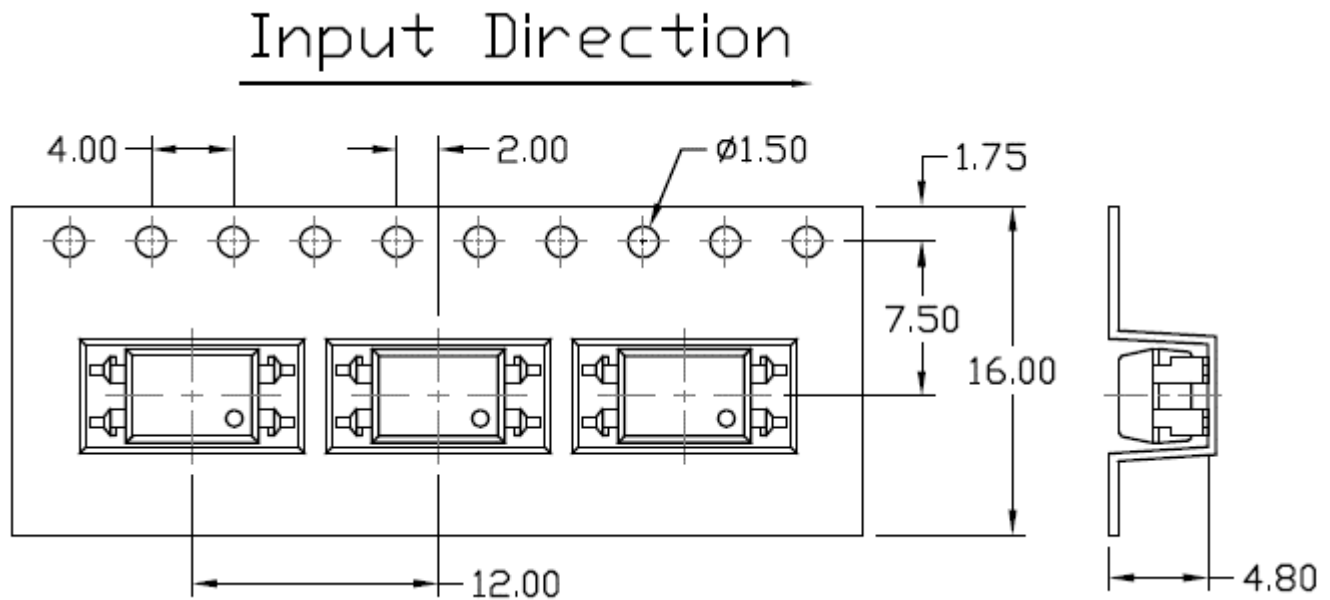


DC Input 4-Pin Phototransistor Optocoupler

Option S(T3) & SL(T3)



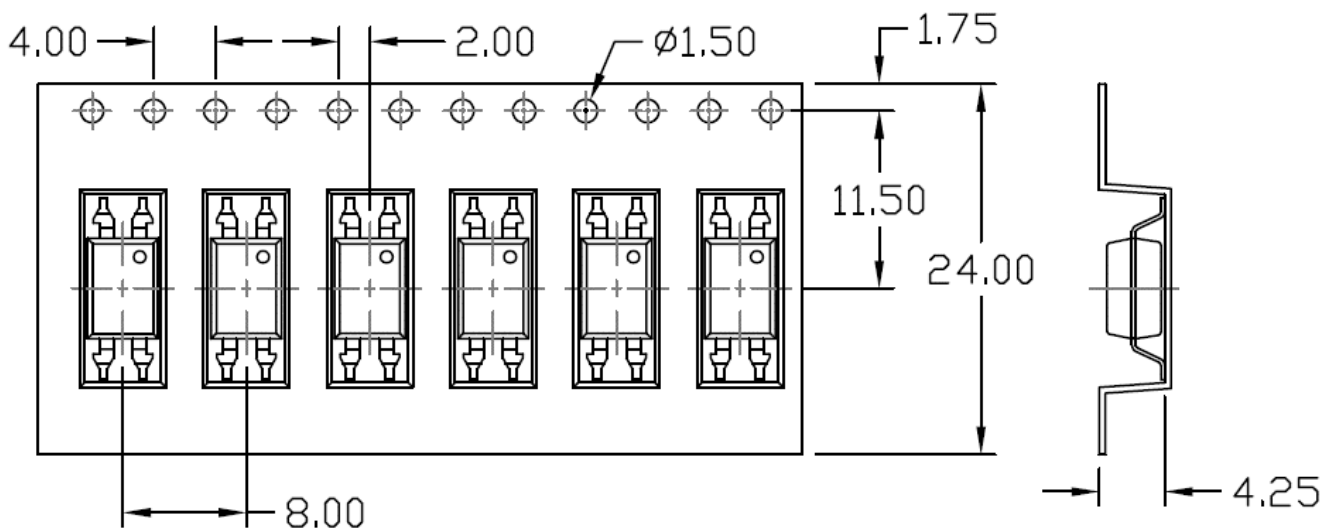
Option S(T4) & SL(T4)





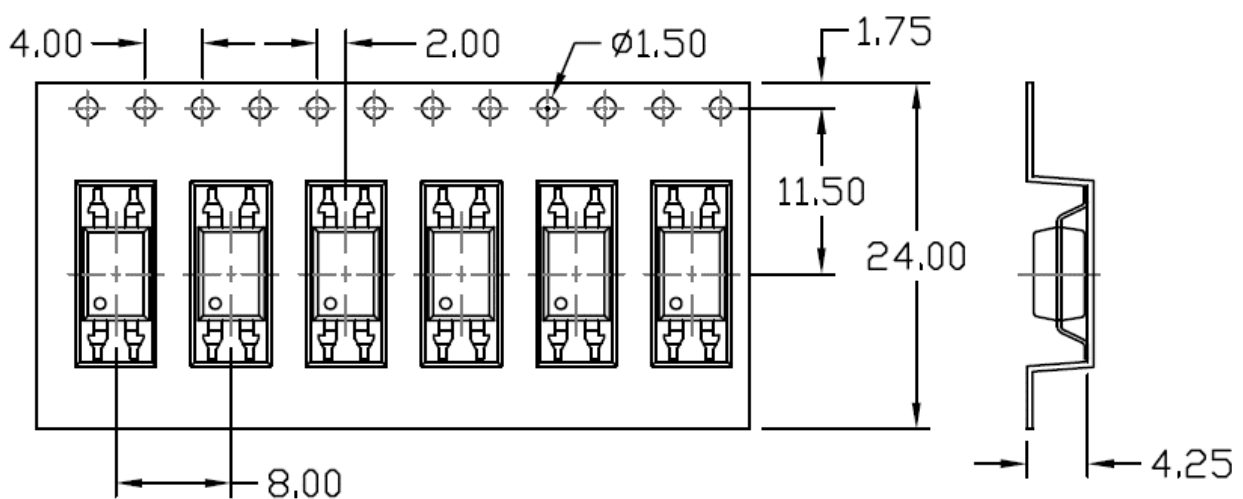
Option SLM(T1)

Input Direction



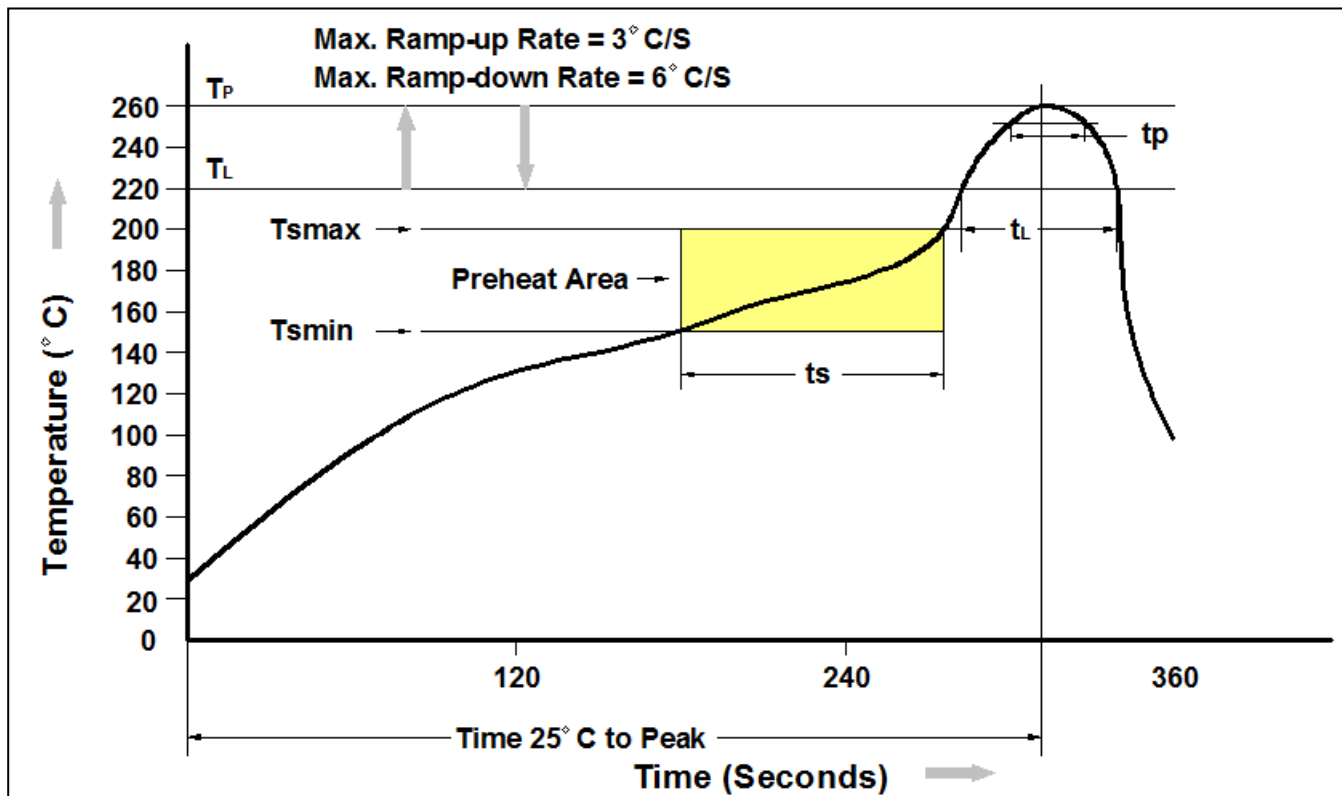
Option SLM(T2)

Input Direction





Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60-120 seconds
Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of 260°C	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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